120 Watt, 2 GHz, Si LDMOS RF power transistor for PCS base station applications

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The structure and performance of a 120 W, 2 GHz, Si RF LDMOS power transistor are described suitable for personal communication systems base station power amplifiers operating in the 1.8-2.2 GHz frequency band. The high gain (10.6 dB at 120 W CW, 2 GHz), and excellent linearity of this transistor, when operated in class-AB, (typically -30 dBc two-tone intermodulation distortion at 120 W PEP) makes it eminently suitable for amplification of digitally modulated signals.

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